

74AHC244; 74AHCT244

Octal buffer/line driver; 3-state

Rev. 05 — 20 December 2007

Product data sheet

1. General description

The 74AHC244; 74AHCT244 is a high-speed Si-gate CMOS device.

The 74AHC244; 74AHCT244 has octal non-inverting buffer/line drivers with 3-state outputs. The 3-state outputs are controlled by the output enable inputs ($\overline{\text{nOE}}$). A HIGH on $\overline{\text{nOE}}$ causes the outputs to assume a high-impedance OFF-state.

2. Features

- Balanced propagation delays
- All inputs have a Schmitt-trigger action
- Inputs accept voltages higher than V_{CC}
- For 74AHC244 only: operates with CMOS input levels
- For 74AHCT244 only: operates with TTL input levels
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC244D 74AHCT244D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC244PW 74AHCT244PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC244BQ 74AHCT244BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85\text{ mm}$	SOT764-1

4. Functional diagram

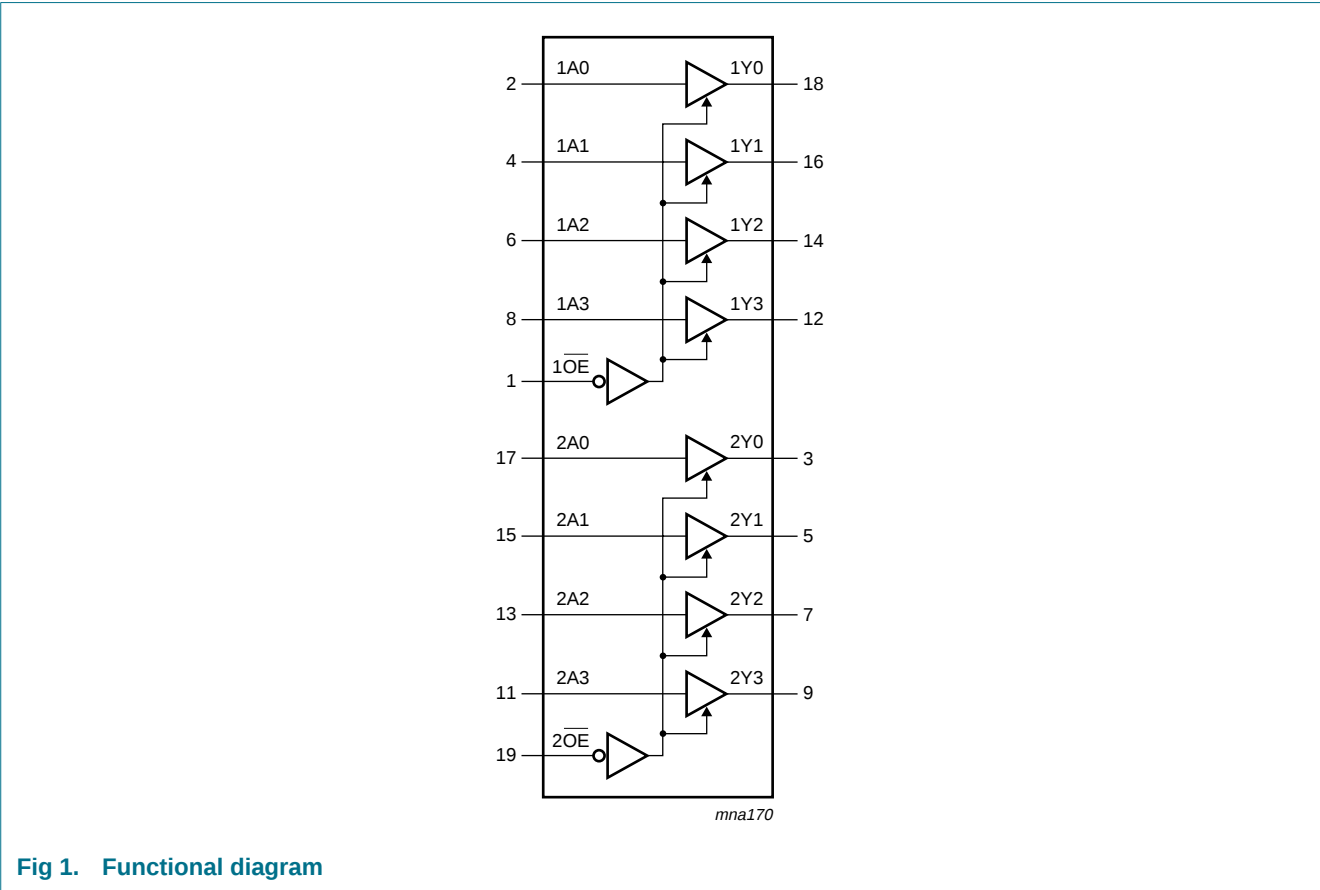


Fig 1. Functional diagram

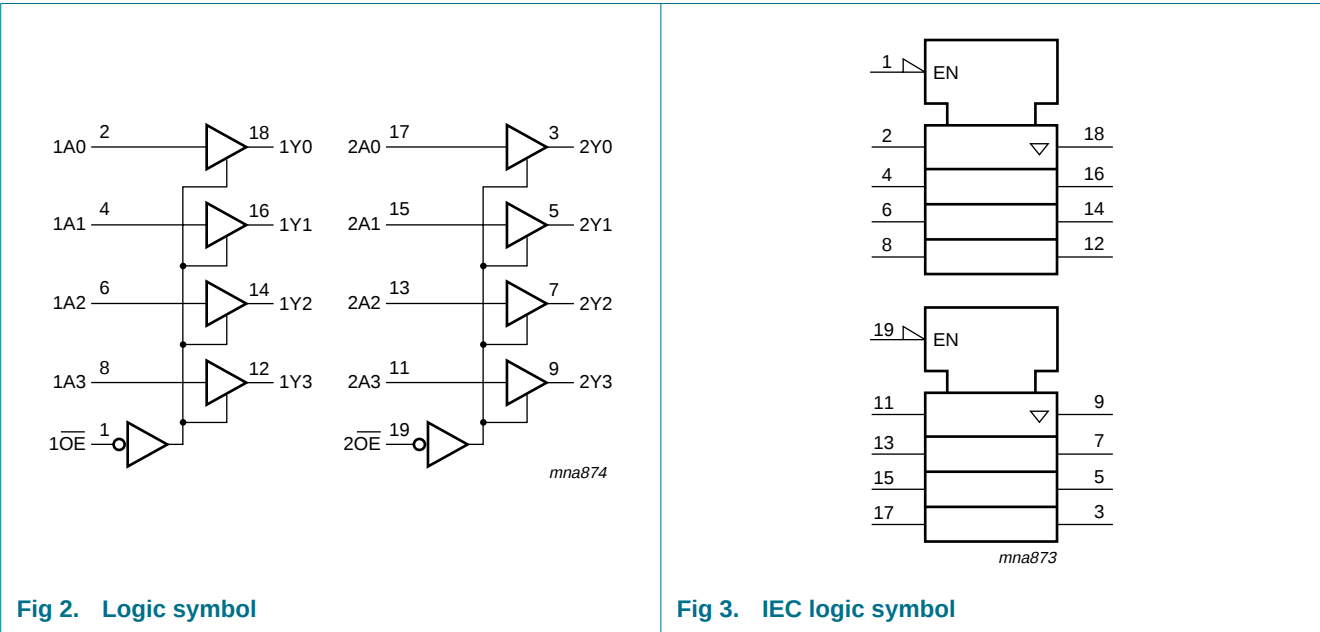
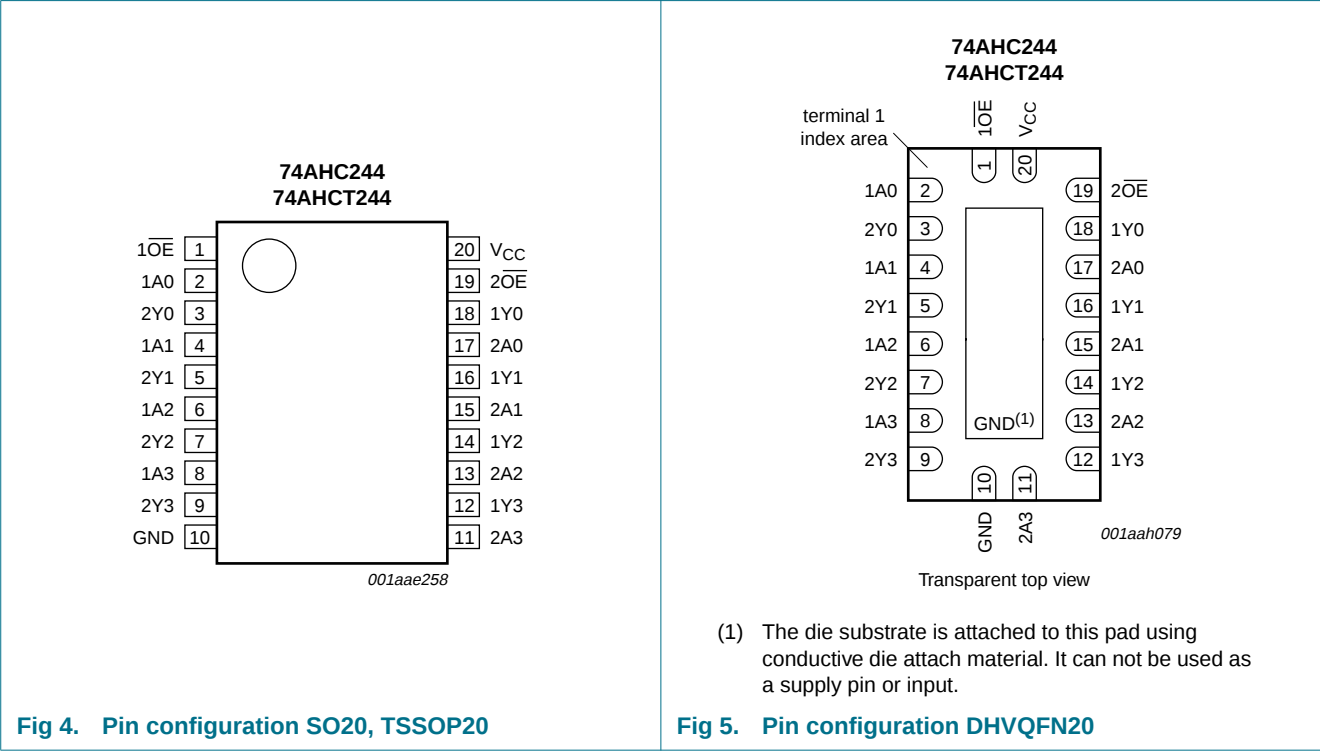


Fig 2. Logic symbol

Fig 3. IEC logic symbol

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1OE	1	output enable input (active LOW)
1A[0:3]	2, 4, 6, 8	data input
2A[0:3]	17, 15, 13, 11	data input
1Y[0:3]	18, 16, 14, 12	data output
2Y[0:3]	3, 5, 7, 9	data output
GND	10	ground (0 V)
2OE	19	output enable input (active LOW)
VCC	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Control	Input	Output
$\overline{\text{nOE}}$	nAn	nYn
L	L	L
	H	H
H	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$	^[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	^[1] -	±20	mA
I_O	output current	$V_O = -0.5 \text{ V}$ to $(V_{CC} + 0.5 \text{ V})$	-	±25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40 \text{ °C}$ to $+125 \text{ °C}$			
	SO20 package		^[2] -	500	mW
	TSSOP20 package		^[3] -	500	mW
	DHVQFN20 package		^[4] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] P_{tot} derates linearly with 8 mW/K above 70 °C.
 [3] P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 [4] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC244			74AHCT244			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V _I	input voltage		0	-	5.5	0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 3.3 V ± 0.3 V	-	-	100	-	-	-	ns/V
		V _{CC} = 5.0 V ± 0.5 V	-	-	20	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	

For type 74AHC244

V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -50 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -50 µA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = -50 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
V _{OL}	LOW-level output voltage	I _O = -8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
		V _I = V _{IH} or V _{IL}								
		I _O = 50 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
I _{OZ}	OFF-state output current	I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.25	-	±2.5	-	±10.0	µA
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA

Table 6. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	3.0	10	-	10	-	10	pF
C _O	output capacitance		-	4.0	-	-	-	-	-	pF
For type 74AHCT244										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _{OZ}	OFF-state output current	per input pin; V _I = V _{IH} or V _{IL} ; V _{CC} = 5.5 V; I _O = 0 A V _O = V _{CC} or GND; other pins at V _{CC} or GND	-	-	±0.25	-	±2.5	-	±10.0	µA
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; I _O = 0 A; other pins at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4.0	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V. For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
For type 74AHC244										
t _{pd}	propagation delay	nAn to nYn; see Figure 6 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.0	8.4	1.0	10.0	1.0	10.5	ns
		C _L = 50 pF	-	7.0	11.9	1.0	13.5	1.0	15.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.4	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		5.0	7.5	1.0	8.5	1.0	9.5	ns
t _{en}	enable time	nOE to nYn; see Figure 7 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	6.5	10.6	1.0	12.5	1.0	13.5	ns
		C _L = 50 pF	-	7.5	14.1	1.0	16.0	1.0	18.0	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	4.0	7.3	1.0	8.5	1.0	9.5	ns
		C _L = 50 pF	-	5.5	9.3	1.0	10.5	1.0	12.0	ns
t _{dis}	disable time	nOE to nYn; see Figure 7 ^[2]								
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	5.5	9.7	1.0	11.0	1.0	12.5	ns
		C _L = 50 pF	-	10.0	14.0	1.0	16.0	1.0	17.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	4.8	7.2	1.0	8.5	1.0	9.0	ns
		C _L = 50 pF	-	7.0	9.2	1.0	10.5	1.0	11.5	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC} ^[3]	-	10	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued
 GND = 0 V. For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
For type 74AHCT244										
t _{pd}	propagation delay	nAn to nYn; see Figure 6 ^[2]								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.5	7.4	1.0	8.5	1.0	9.5	ns
		C _L = 50 pF	-	5.0	8.4	1.0	9.5	1.0	10.5	ns
t _{en}	enable time	n $\overline{\text{OE}}$ to nYn; see Figure 7								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	3.5	10.4	1.0	12.0	1.0	13.0	ns
		C _L = 50 pF	-	5.5	11.4	1.0	13.0	1.0	14.5	ns
t _{dis}	disable time	n $\overline{\text{OE}}$ to nYn; see Figure 7 ^[2]								
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	5.0	9.4	1.0	10.0	1.0	12.0	ns
		C _L = 50 pF	-	7.0	11.4	1.0	13.0	1.0	14.5	ns
C _{PD}	power dissipation capacitance	per buffer; ^[3] C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	-	12	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3 \text{ V}$ and $V_{CC} = 5.0 \text{ V}$).

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

t_{en} is the same as t_{PZL} and t_{PZH} .

t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[3] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

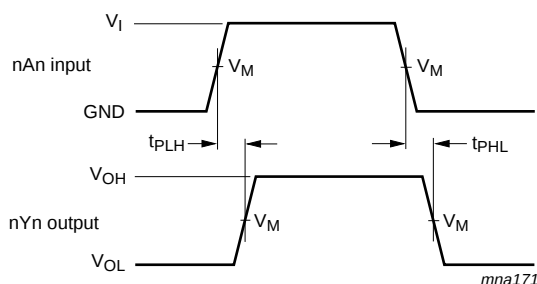
f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

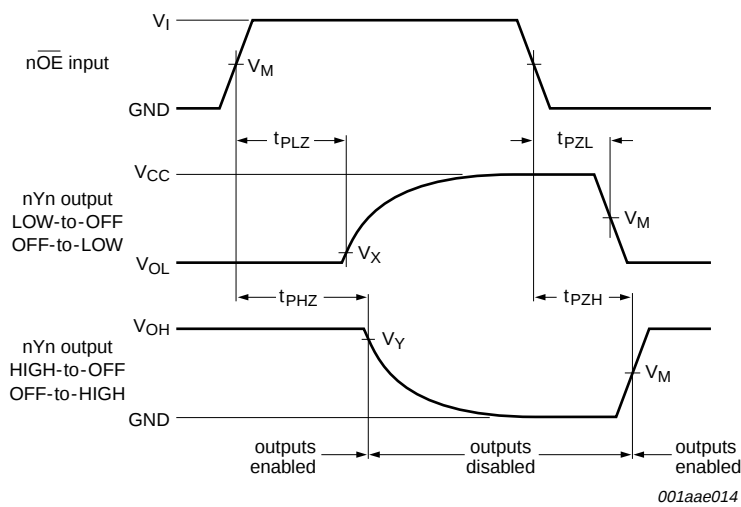
11. Waveforms



Measurement points are given in [Table 8](#).

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay input (nAn) to output (nYn)

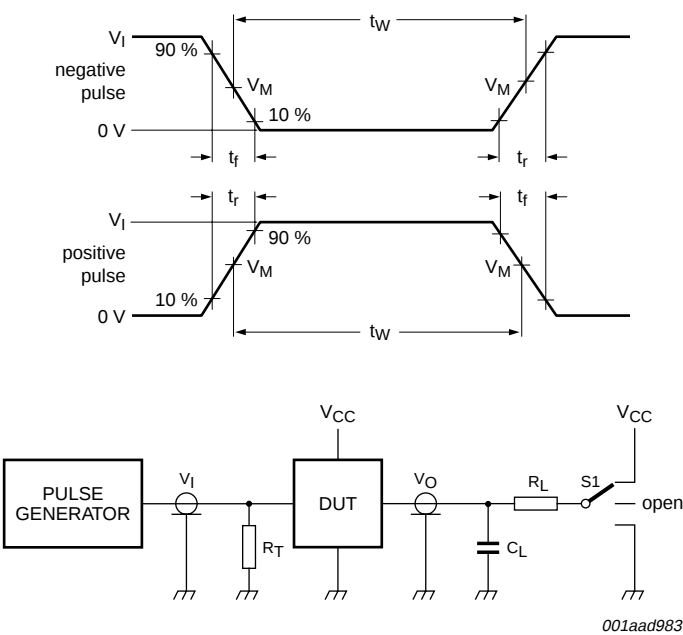


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. enable and disable times

Table 8. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74AHC244	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
74AHCT244	1.5 V	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$



Test data is given in [Table 9](#).
Definitions test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator
 C_L = Load capacitance including jig and probe capacitance
 R_L = Load resistor
 $S1$ = Test selection switch

Fig 8. Load circuitry for switching times

Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74AHC244	V_{CC}	3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74AHCT244	3.0 V	3.0 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

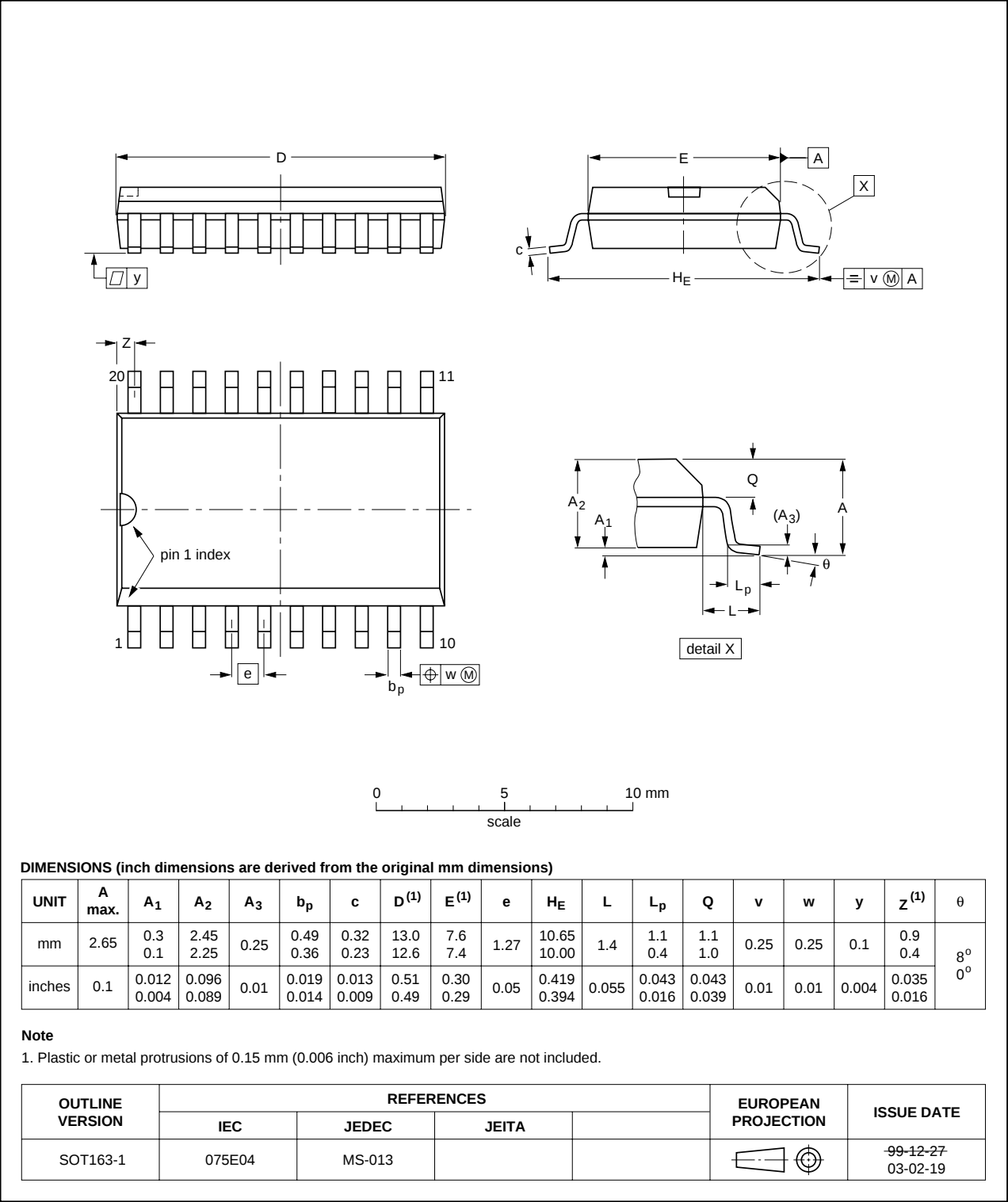


Fig 9. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

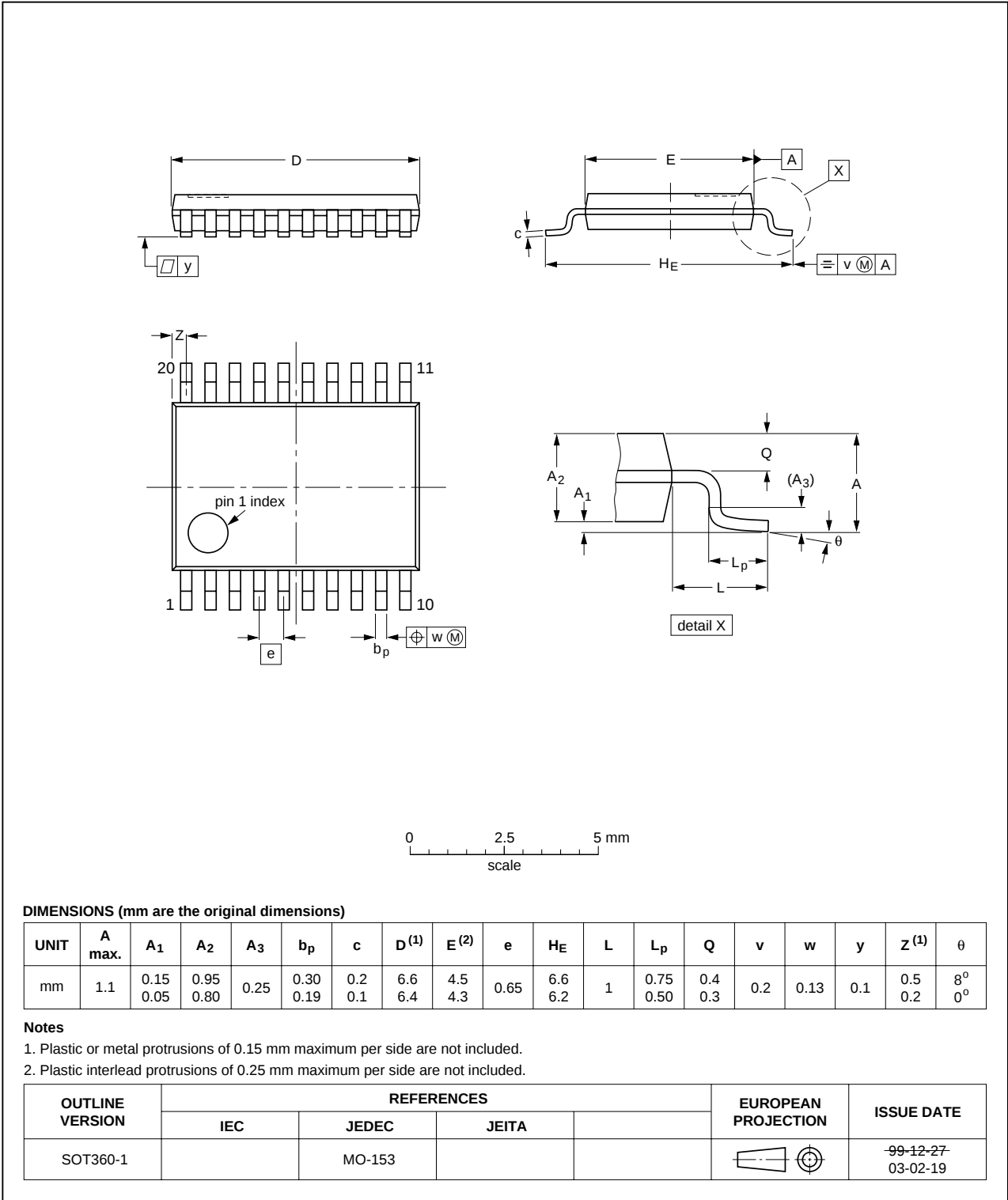


Fig 10. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

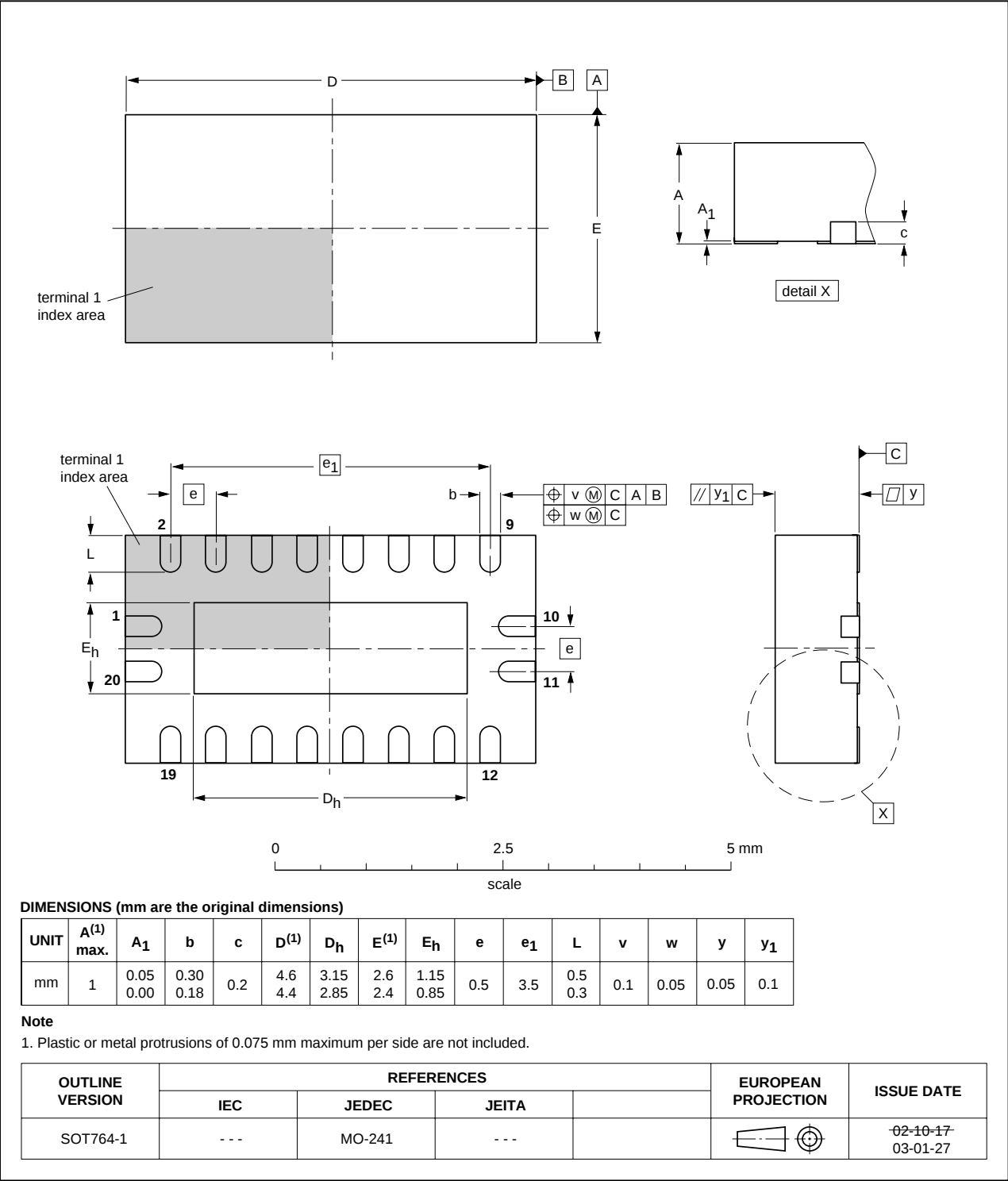


Fig 11. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charge Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT244_5	20071220	Product data sheet	-	74AHC_AHCT244_4
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3: DHVQFN20 package added. • Section 7: derating values added for DHVQFN20 package. • Section 12: outline drawing added for DHVQFN20 package.			
74AHC_AHCT244_4	20060210	Product data sheet	-	74AHC_AHCT244_3
74AHC_AHCT244_3	19990928	Product specification	-	74AHC_AHCT244_2
74AHC_AHCT244_2	19990224	Product specification	-	74AHC_AHCT244_1
74AHC_AHCT244_1	19980921	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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